

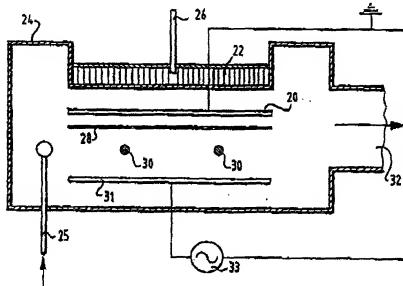
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(54) Title: SEMICONDUCTING DEVICES AND METHOD OF MAKING THEREOF



(57) Abstract

The invention relates to a process for providing a semiconductor device comprising the steps of depositing a semiconductor layer onto a substrate by means of heating a gas to a predetermined, dissociation temperature so that the gas dissociates into fractions, whereby these fractions subsequently condense on the substrate to build up a semiconductor layer.